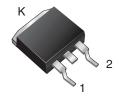
MBRB25H35CT, MBRB25H45CT, MBRB25H60CT

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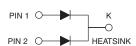
# **Dual Common Cathode Schottky Rectifier**

High Barrier Technology for Improved High Temperature Performance

## D<sup>2</sup>PAK (TO-263AB)



### MBRB25HxxCT



### **DESIGN SUPPORT TOOLS**



| L | click | logo | to get | started | 1 |
|---|-------|------|--------|---------|---|
|   |       |      |        |         | ~ |



| PRIMARY CHARACTERISTICS     |                               |  |  |  |  |
|-----------------------------|-------------------------------|--|--|--|--|
| I <sub>F(AV)</sub> 2 x 15 A |                               |  |  |  |  |
| V <sub>RRM</sub>            | 35 V, 45 V, 60 V              |  |  |  |  |
| I <sub>FSM</sub>            | 150 A                         |  |  |  |  |
| VF                          | 0.54 V, 0.60 V                |  |  |  |  |
| I <sub>R</sub>              | 100 µA                        |  |  |  |  |
| T <sub>J</sub> max.         | 175 °C                        |  |  |  |  |
| Package                     | D <sup>2</sup> PAK (TO-263AB) |  |  |  |  |
| Circuit configuration       | Common cathode                |  |  |  |  |

## FEATURES

- Power pack
- Guardring for overvoltage protection
- Lower power losses, high efficiency
- Low forward voltage drop
- · Low leakage current
- High forward surge capability
- High frequency operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245  $^{\circ}\mathrm{C}$
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### **TYPICAL APPLICATIONS**

For use in low voltage, high frequency rectifier of switching mode power supplies, freewheeling diodes, DC/DC converters, or polarity protection application.

### **MECHANICAL DATA**

Case: D<sup>2</sup>PAK (TO-263AB)

Molding compound meets UL 94 V-0 flammability rating Base P/NHE3\_X - RoHS-compliant, AEC-Q101 qualified ("\_X" denotes revision code, e.g. A, B, ...)

**Terminals:** matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

HE3 suffix meets JESD 201 class 2 whisker test **Polarity:** as marked

| <b>MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C unless otherwise noted)                       |                          |             |             |             |      |  |  |
|--|--------------------------|-------------|-------------|-------------|------|--|--|
| PARAMETER  |                          | MBRB25H35CT | MBRB25H45CT | MBRB25H60CT | UNIT |  |  |
| Maximum repetitive peak reverse voltage  | V <sub>RRM</sub>         | 35          | 45          | 60          |      |  |  |
| Working peak reverse voltage   | V <sub>RWM</sub>         | 35          | 45          | 60          | V    |  |  |
| Maximum DC blocking voltage  | V <sub>DC</sub>          | 35          | 45          | 60          |      |  |  |
| total c  | levice                   | 30          |             |             |      |  |  |
| Max. average forward rectified current (fig. 1) per diode                                    |                          | 15          |             |             |      |  |  |
| Non-repetitive avalanche energy per diode at 25 °C, $I_{AS}$ = 4 A, L = 10 mH                | E <sub>AS</sub>          | 80          |             |             | mJ   |  |  |
| Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode | I <sub>FSM</sub>         | 150         |             |             | А    |  |  |
| Peak repetitive reverse surge current per diode at $t_p = 1 \text{ kHz}$                     | 2.0 µs, I <sub>RRM</sub> | 1.0         | 1.0         | 0.5         | А    |  |  |
| Peak non-repetitive reverse energy (8/20 µs waveform   | n) E <sub>RSM</sub>      | 25          | 25          | 20          | mJ   |  |  |
| Electrostatic discharge capacitor voltage Human body model: C = 100 pF, R = 1.5 k $\Omega$   |                          | 25          |             |             | kV   |  |  |
| Voltage rate of change (rated V <sub>R</sub> )   |                          | 10 000      |             |             | V/µs |  |  |
| Operating junction and storage temperature range   |                          | -65 to +175 |             |             | °C   |  |  |

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1

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| <b>ELECTRICAL CHARACTERISTICS</b> ( $T_c = 25 \degree C$ unless otherwise noted) |                               |                       |                         |                            |      |             |      |      |  |
|--|-------------------------------|-----------------------|-------------------------|----------------------------|------|-------------|------|------|--|
| PARAMETER  | SYMBOL                        | TEST CONDITIONS       |                         | MBRB25H35CT<br>MBRB25H45CT |      | MBRB25H60CT |      | UNIT |  |
|  |                               |                       |                         |                            | MAX. | TYP.        | MAX. |      |  |
|  | V <sub>F</sub> <sup>(1)</sup> | I <sub>F</sub> = 15 A | $T_J = 25 \ ^\circ C$   | -                          | 0.64 | -           | 0.70 | V    |  |
| Maximum instantaneous forward voltage  |                               |                       | T <sub>J</sub> = 125 °C | 0.50                       | 0.54 | 0.56        | 0.60 |      |  |
| per diode  | VF ()                         | I <sub>F</sub> = 30 A | T <sub>J</sub> = 25 °C  | -                          | 0.74 | -           | 0.85 |      |  |
|  |                               |                       | T <sub>J</sub> = 125 °C | 0.63                       | 0.67 | 0.68        | 0.72 |      |  |
| Maximum reverse current per diode  | I <sub>B</sub> <sup>(2)</sup> | Rated V <sub>B</sub>  | $T_J = 25 \ ^\circ C$   | -                          | 100  | -           | 100  | μA   |  |
| Maximum reverse current per diode  | 'H (=/                        | naleu v <sub>R</sub>  | T <sub>J</sub> = 125 °C | 6.0                        | 20   | 4.0         | 20   | mA   |  |

#### Notes

 $^{(1)}\,$  Pulse test: 300  $\mu s$  pulse width, 1 % duty cycle

<sup>(2)</sup> Pulse test: pulse width  $\leq$  40 ms

| <b>THERMAL CHARACTERISTICS</b> ( $T_C = 25 \text{ °C}$ unless otherwise noted) |                 |      |      |  |  |  |  |
|--|-----------------|------|------|--|--|--|--|
| PARAMETER  | SYMBOL          | MBRB | UNIT |  |  |  |  |
| Thermal resistance, junction to case per diode                                 | $R_{\theta JC}$ | 1.5  | °C/W |  |  |  |  |

| ORDERING INFORMATION (Example) |                                   |                 |              |               |               |  |  |
|--------------------------------|-----------------------------------|-----------------|--------------|---------------|---------------|--|--|
| PACKAGE                        | PREFERRED P/N                     | UNIT WEIGHT (g) | PACKAGE CODE | BASE QUANTITY | DELIVERY MODE |  |  |
| TO-263AB                       | MBRB25H60CTHE3_B/P <sup>(1)</sup> | 1.35            | Р            | 50/tube       | Tube          |  |  |
| TO-263AB                       | MBRB25H60CTHE3_B/I <sup>(1)</sup> | 1.35            | Ι            | 800/reel      | Tape and reel |  |  |

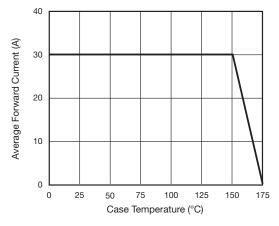
#### Note

(1) AEC-Q101 qualified

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## **RATINGS AND CHARACTERISTICS CURVES** ( $T_C = 25$ °C unless otherwise noted)



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Fig. 1 - Forward Derating Curve (Total)

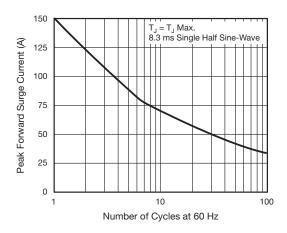


Fig. 2 - Maximum Non-Repetitive Peak Forward Surge Current Per Diode

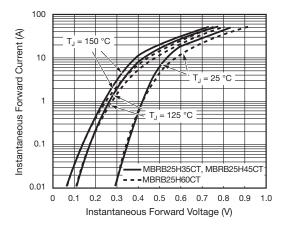


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

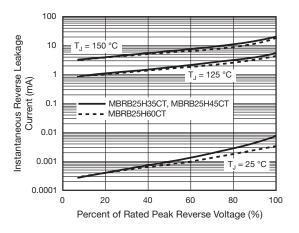


Fig. 4 - Typical Reverse Characteristics Per Diode

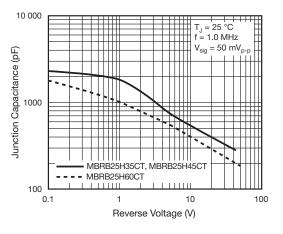


Fig. 5 - Typical Junction Capacitance Per Diode

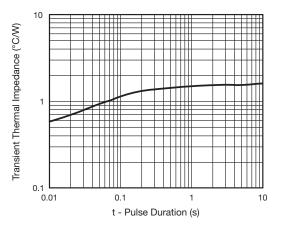


Fig. 6 - Typical Transient Thermal Impedance Per Diode

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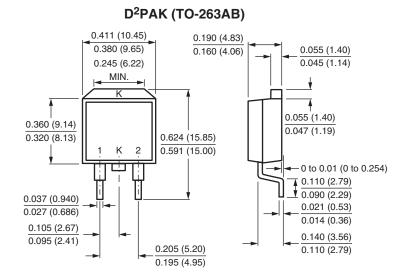
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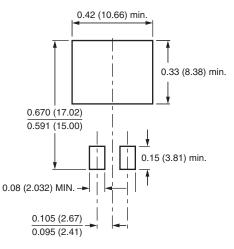
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## **PACKAGE OUTLINE DIMENSIONS** in inches (millimeters)



## **Mounting Pad Layout**





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